

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(on)</sub> Max       | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|----------------------------------------------|
| 80V               | 7.0mΩ @ V <sub>GS</sub> = 10V | 95A                                          |
|                   | 11mΩ @ V <sub>GS</sub> = 4.5V | 75A                                          |

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

## Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

## Features

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Low R<sub>DS(on)</sub> – Minimizes Power Losses
- Low Q<sub>g</sub> – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us) or your local Diodes representative.  
<https://www.diodes.com/quality/product-definitions/>

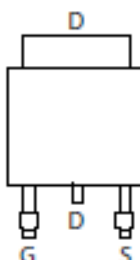
## Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)

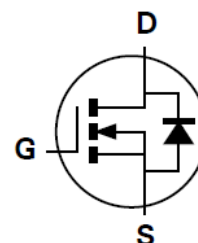
TO252 (DPAK)



Top View



Pin Out  
Top View



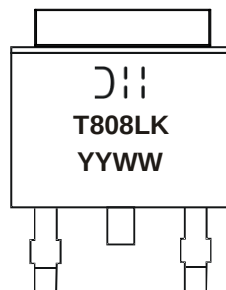
Equivalent Circuit

## Ordering Information

| Part Number   | Package      | Packing |             |
|---------------|--------------|---------|-------------|
|               |              | Qty.    | Carrier     |
| DMT8008LK3-13 | TO252 (DPAK) | 2,500   | Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
 T808LK = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 21 = 2021)  
 WW = Week Code (01 to 53)

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                                              | Symbol   | Value                           | Unit |
|-----------------------------------------------------------------------------|----------|---------------------------------|------|
| Drain-Source Voltage                                                        | $V_{DS}$ | 80                              | V    |
| Gate-Source Voltage                                                         | $V_{GS}$ | $\pm 20$                        | V    |
| Continuous Drain Current, $V_{GS} = 10\text{V}$                             | $I_D$    | $T_C = +25^\circ\text{C}$<br>95 | A    |
|                                                                             |          | $T_C = +70^\circ\text{C}$<br>76 |      |
| Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)              | $I_{DM}$ | 380                             | A    |
| Maximum Continuous Body Diode Forward Current (Note 6)                      | $I_S$    | 95                              | A    |
| Pulsed Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%) | $I_{SM}$ | 380                             | A    |
| Avalanche Current, $L = 0.1\text{mH}$                                       | $I_{AS}$ | 23                              | A    |
| Avalanche Energy, $L = 0.1\text{mH}$                                        | $E_{AS}$ | 26.5                            | mJ   |

## Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                   | Symbol          | Value       | Unit               |
|--------------------------------------------------|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5)                 | $P_D$           | 1.7         | W                  |
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{\theta JA}$ | 71          | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 6)                 | $P_D$           | 3           | W                  |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{\theta JA}$ | 45          | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case             | $R_{\theta JC}$ | 1.1         |                    |
| Operating and Storage Temperature Range          | $T_J, T_{STG}$  | -55 to +150 | $^\circ\text{C}$   |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                          | Symbol       | Min | Typ  | Max       | Unit       | Test Condition                                               |
|-----------------------------------------|--------------|-----|------|-----------|------------|--------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 7)</b>     |              |     |      |           |            |                                                              |
| Drain-Source Breakdown Voltage          | $BV_{DSS}$   | 80  | —    | —         | V          | $V_{GS} = 0V, I_D = 1mA$                                     |
| Zero Gate Voltage Drain Current         | $I_{DSS}$    | —   | —    | 1         | $\mu A$    | $V_{DS} = 64V, V_{GS} = 0V$                                  |
| Gate-Source Leakage                     | $I_{GSS}$    | —   | —    | $\pm 100$ | nA         | $V_{GS} = \pm 20V, V_{DS} = 0V$                              |
| <b>ON CHARACTERISTICS (Note 7)</b>      |              |     |      |           |            |                                                              |
| Gate Threshold Voltage                  | $V_{GS(th)}$ | 1.3 | —    | 2.8       | V          | $V_{DS} = V_{GS}, I_D = 250\mu A$                            |
| Static Drain-Source On-Resistance       | $R_{DS(on)}$ | —   | 5.6  | 7.0       | m $\Omega$ | $V_{GS} = 10V, I_D = 14A$                                    |
|                                         |              | —   | 7.9  | 11        |            | $V_{GS} = 4.5V, I_D = 12A$                                   |
| Diode Forward Voltage                   | $V_{SD}$     | —   | 0.8  | 1.2       | V          | $V_{GS} = 0V, I_S = 20A$                                     |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b> |              |     |      |           |            |                                                              |
| Input Capacitance                       | $C_{iss}$    | —   | 2345 | —         | pF         | $V_{DS} = 40V, V_{GS} = 0V,$<br>$f = 1MHz$                   |
| Output Capacitance                      | $C_{oss}$    | —   | 842  | —         |            |                                                              |
| Reverse Transfer Capacitance            | $C_{rss}$    | —   | 52   | —         |            |                                                              |
| Gate Resistance                         | $R_g$        | —   | 1.7  | —         | $\Omega$   | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$                         |
| Total Gate Charge ( $V_{GS} = 4.5V$ )   | $Q_g$        | —   | 21.7 | —         | nC         | $V_{DD} = 40V, I_D = 2A$                                     |
| Total Gate Charge ( $V_{GS} = 10V$ )    | $Q_g$        | —   | 41.2 | —         |            |                                                              |
| Gate-Source Charge                      | $Q_{gs}$     | —   | 5.0  | —         |            |                                                              |
| Gate-Drain Charge                       | $Q_{gd}$     | —   | 10.6 | —         |            |                                                              |
| Turn-On Delay Time                      | $t_{D(on)}$  | —   | 5.8  | —         | ns         | $V_{DD} = 40V, V_{GS} = 10V,$<br>$I_D = 2A, R_G = 1.6\Omega$ |
| Turn-On Rise Time                       | $t_R$        | —   | 5.4  | —         |            |                                                              |
| Turn-Off Delay Time                     | $t_{D(off)}$ | —   | 24.5 | —         |            |                                                              |
| Turn-Off Fall Time                      | $t_F$        | —   | 43.2 | —         |            |                                                              |
| Body Diode Reverse Recovery Time        | $t_{RR}$     | —   | 61   | —         | ns         | $I_F = 2A, di/dt = 100A/\mu s$                               |
| Body Diode Reverse Recovery Charge      | $Q_{RR}$     | —   | 181  | —         | nC         |                                                              |

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

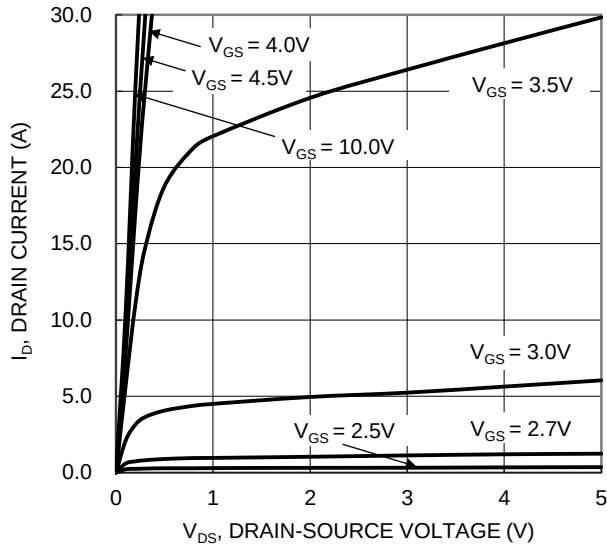


Figure 1. Typical Output Characteristic

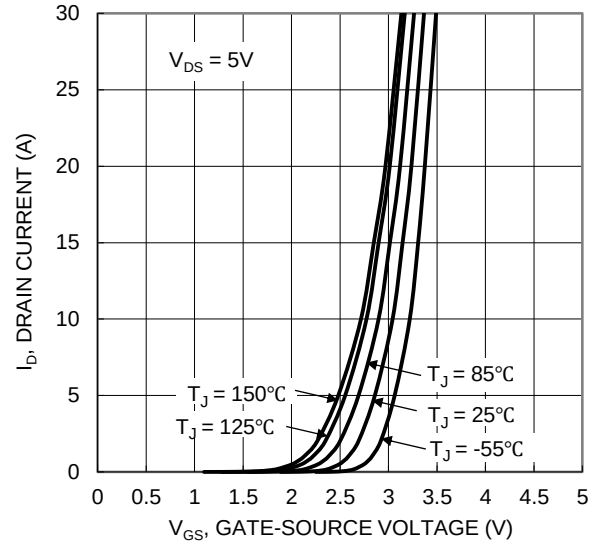


Figure 2. Typical Transfer Characteristic

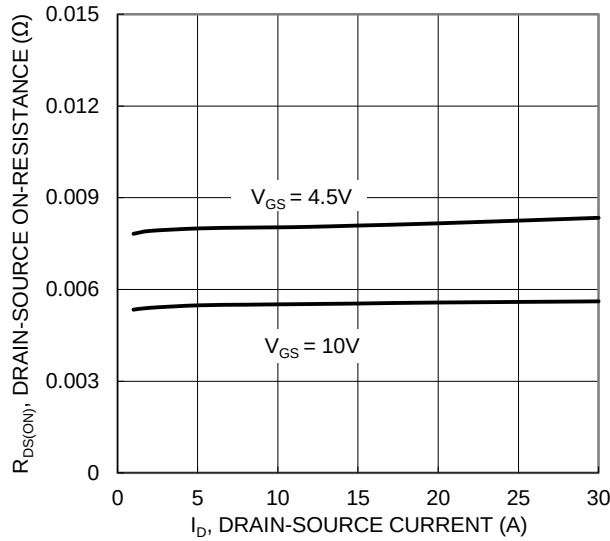


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

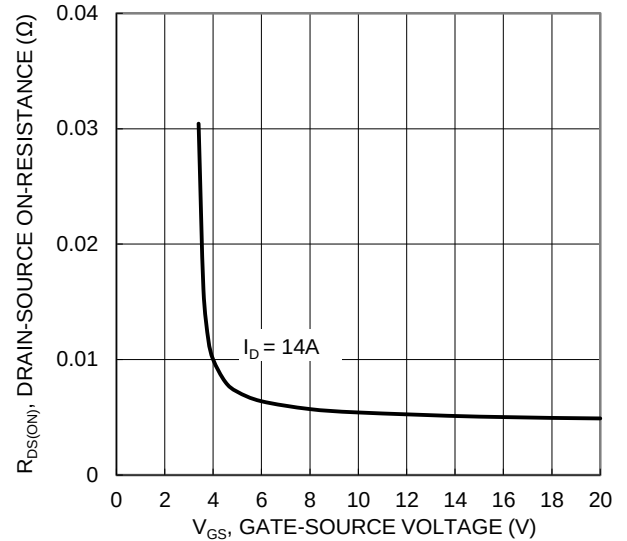


Figure 4. Typical Transfer Characteristic

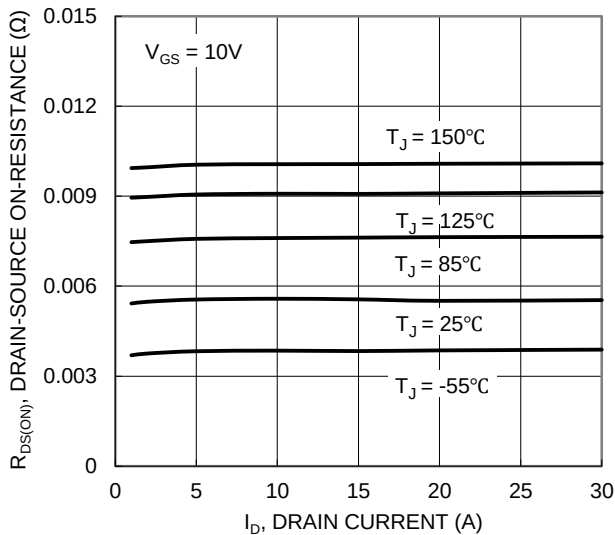


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

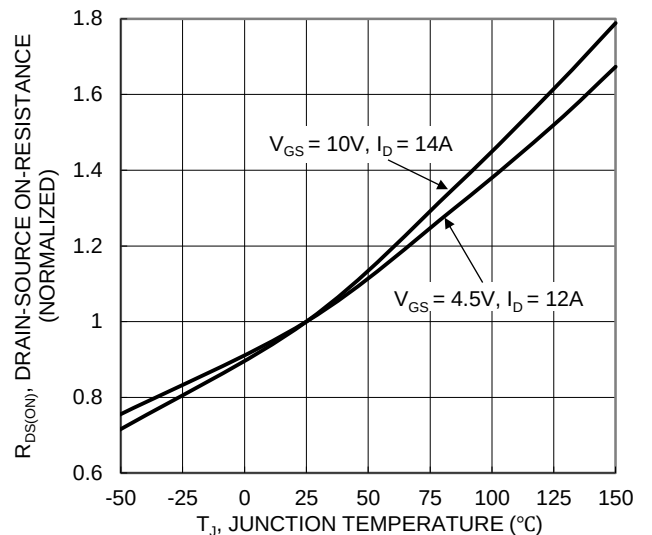


Figure 6. On-Resistance Variation with Junction Temperature

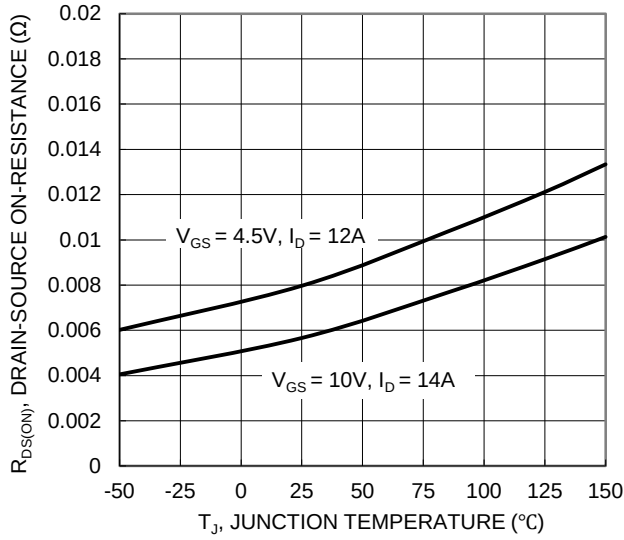


Figure 7. On-Resistance Variation with Temperature

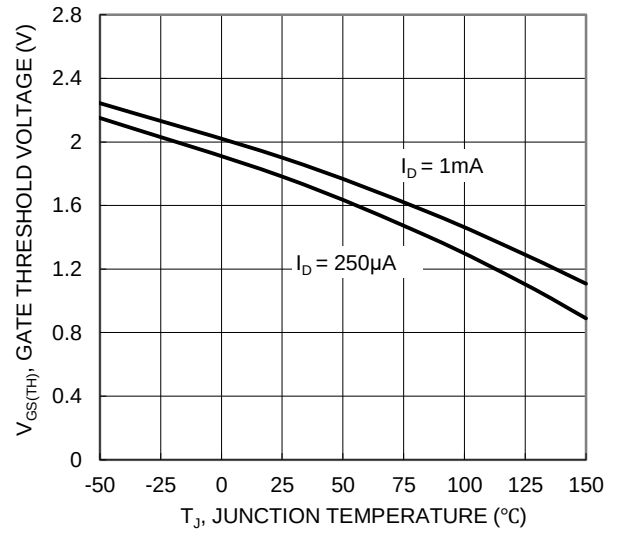


Figure 8. Gate Threshold Variation vs. Temperature

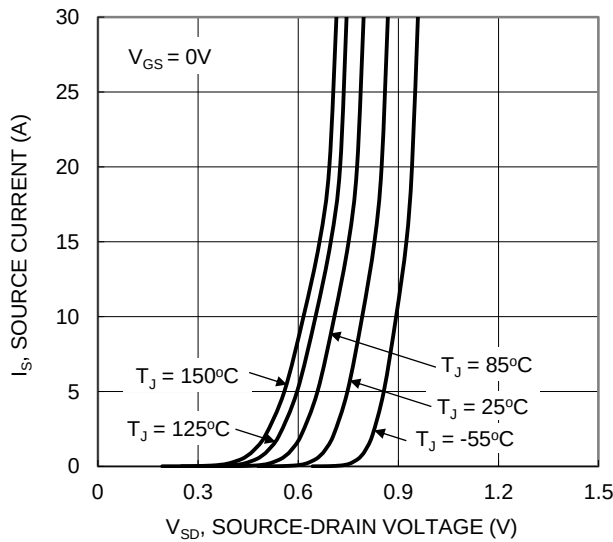


Figure 9. Diode Forward Voltage vs. Current

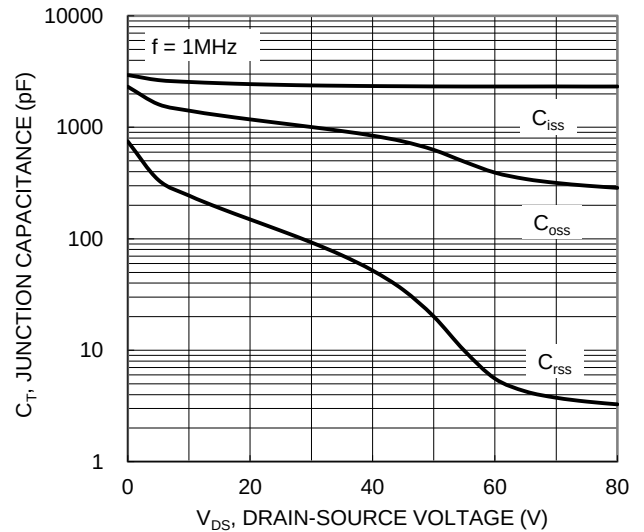


Figure 10. Typical Junction Capacitance

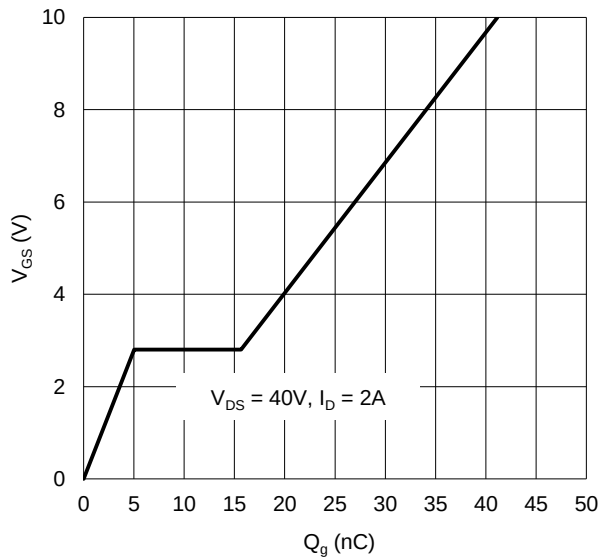


Figure 11. Gate Charge

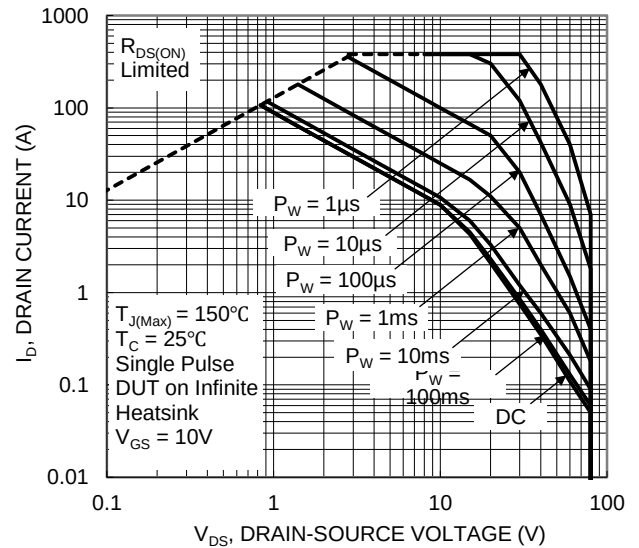


Figure 12. SOA, Safe Operation Area

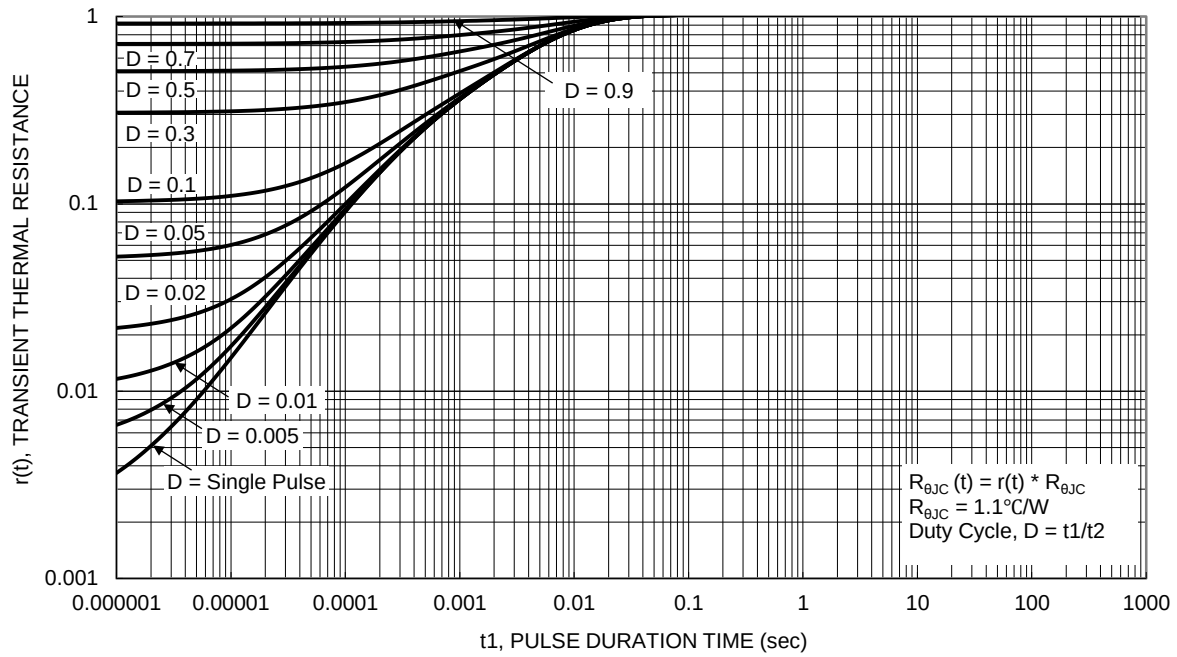
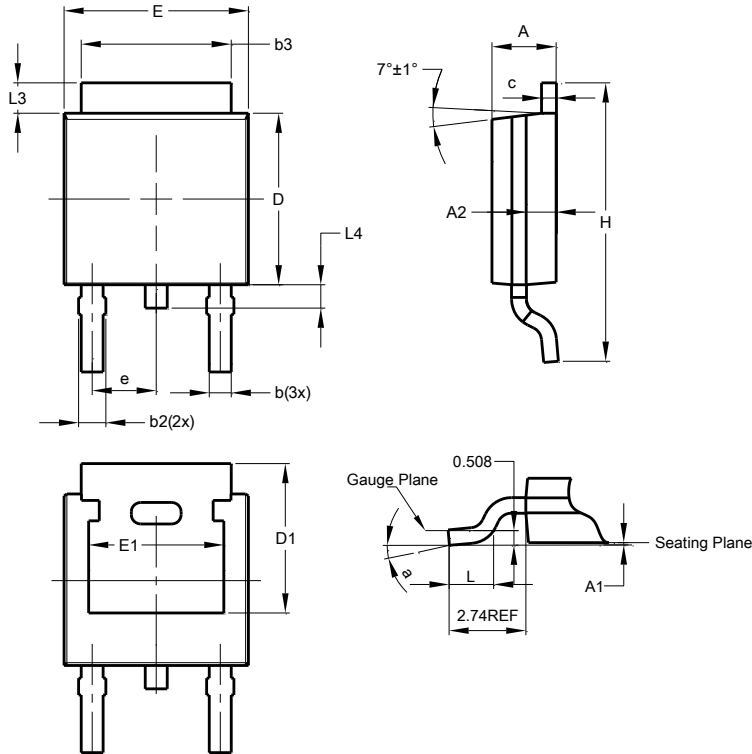


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

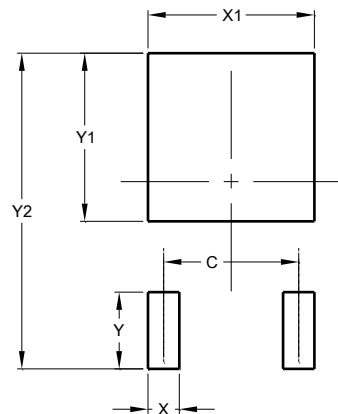


| TO252 (DPAK)         |      |       |       |
|----------------------|------|-------|-------|
| Dim                  | Min  | Max   | Typ   |
| A                    | 2.19 | 2.39  | 2.29  |
| A1                   | 0.00 | 0.13  | 0.08  |
| A2                   | 0.97 | 1.17  | 1.07  |
| b                    | 0.64 | 0.88  | 0.783 |
| b2                   | 0.76 | 1.14  | 0.95  |
| b3                   | 5.21 | 5.46  | 5.33  |
| c                    | 0.45 | 0.58  | 0.531 |
| D                    | 6.00 | 6.20  | 6.10  |
| D1                   | 5.21 | —     | —     |
| e                    | —    | —     | 2.286 |
| E                    | 6.45 | 6.70  | 6.58  |
| E1                   | 4.32 | —     | —     |
| H                    | 9.40 | 10.41 | 9.91  |
| L                    | 1.40 | 1.78  | 1.59  |
| L3                   | 0.88 | 1.27  | 1.08  |
| L4                   | 0.64 | 1.02  | 0.83  |
| a                    | 0°   | 10°   | —     |
| All Dimensions in mm |      |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 4.572         |
| X          | 1.060         |
| X1         | 5.632         |
| Y          | 2.600         |
| Y1         | 5.700         |
| Y2         | 10.700        |

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